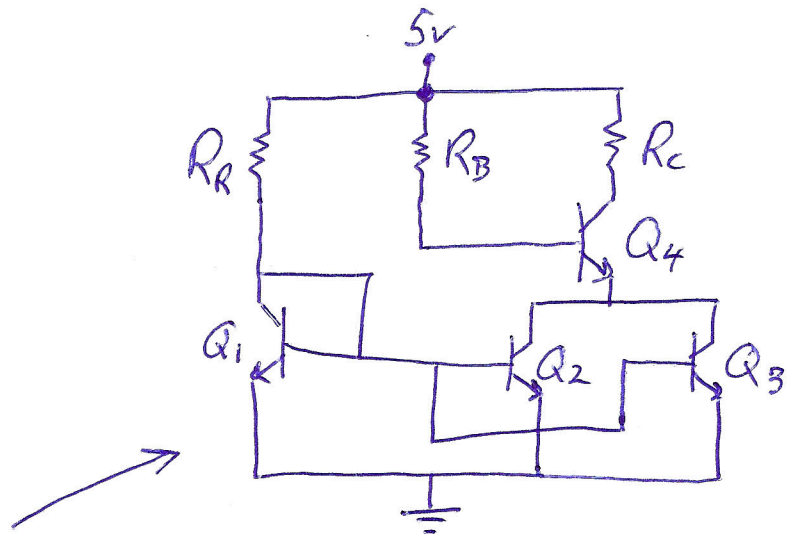


Don't Forget:

- Be sure to include units for all numerical results
- Use standard engineering notation, i.e. report $1.5\mu\text{V}$, *not* 0.0000015V

Question #1:

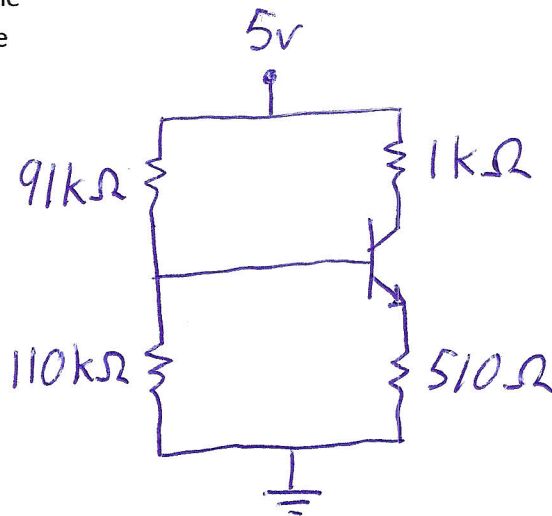
Design the bias circuit shown. Assume $\beta=100$ and $V_A=\infty$. Select values of R_R , R_C , and R_B that cause transistor Q4 to have $V_{CE}=2V$, and $I_C=2mA$. Your design should also ensure that the other transistors are in the active mode for the current mirror to work.



Question #2:

For the circuit shown, assume $\beta=100$ and $V_A=\infty$.

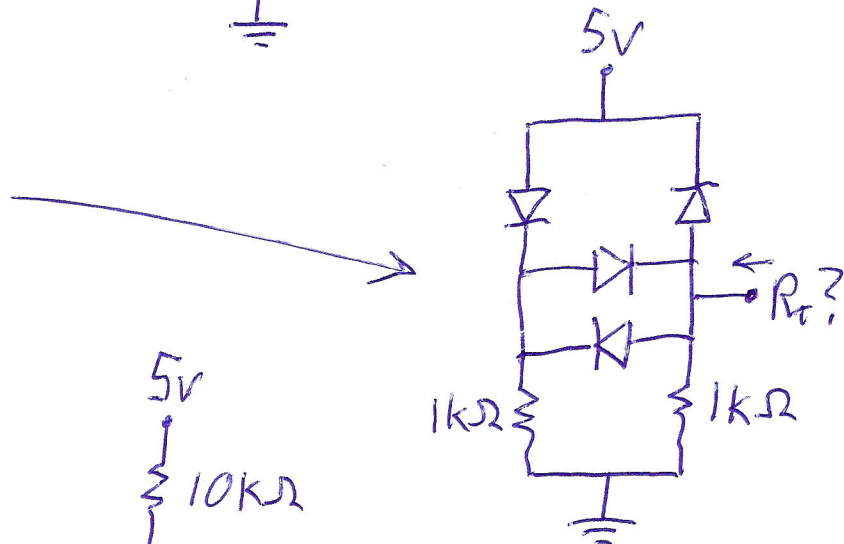
- Find I_C and V_{CE}
- Is this circuit stable with respect to variations in V_{BE} ? Why or why not?
- Is this circuit stable with respect to variations in β ? Why or why not?



Question #3:

For the circuit shown, assume that the diodes have an ideality factor of $n=2$.

- Draw the small signal circuit.
- Find the small signal Thevenin resistance at the node shown.



Question #4:

For the circuit shown, assume $V_{Tn}=1V$, and $\mu_n C_{ox}(W/L)=1 \text{ mA/V}^2$, and $V_A=100V$.

- Find g_m and r_o
- Draw the small signal circuit
- Find the small signal Thevenin resistance at the node shown.

